

### **IN THE CLAIMS**

Please cancel claims 1-13, claim 15, and claims 19-26.

### **REMARKS**

The drawings were objected to. The drawings have been corrected. Lines to label existing regions of the Figures 4G and Figure 4H were added. No new matter has been added to the disclosure by the addition of these labels. The label 20 has been added to correspond to same label on Figure 4C. The label 18 has been added to designate the source region. Finally the label 419 has been added to designate the metal contacts to the source and drain regions. The disclosure was amended to describe the connection of the metal structure 419 to the source region 18 and the buried body diffusion 30. A separate paper requesting approval to amend the drawings accompanies this amendment.

The disclosure was objected to because of informalities. The disclosure has been amended to overcome the objection to the informalities.

Claims 20-22 were rejected under 35 U.S.C. 112, second paragraph, as being indefinite.

Claims 1-5 were rejected under 35 U.S.C. 102(a) as being anticipated by Efland; claims 6, 8, 10, 12, 14, 17, 19 and 23-26 were rejected under 35 U.S.C. 102(a) as being anticipated by Harris; and claims 7, 9, 11, 13, 16 and 18 were rejected under 35 U.S.C. 103(a) as being unpatentable over Harris in view of Efland.

Claims 1-13, claim 15, and claims 19-26 have been cancelled.

Claim 14 has the limitation of a source region connected to a source metallization and a buried diffusion body connected to the source metallization. This feature of the claimed invention is not found in the Harris et al. patent. With regard to claim 14 the examiner states that the Harris et al. patent describes a source metallization 11 that is not directly connected to the buried body diffusion 3. The examiner is aware that each and element of the instant claims must be found in a valid 102 reference. Claim 14 and its dependent claims 16, 17, and 18 are therefore allowable over the cited art.

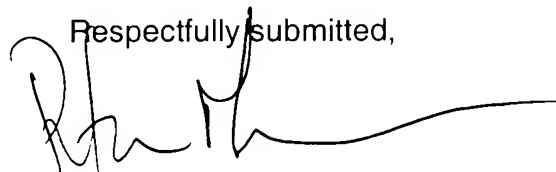
In light of the above, it is respectfully submitted that the present application is in condition for allowance, and notice to that effect is respectfully requested.

While it is believed that the instant response places the application in condition for allowance, should the Examiner have any further comments or suggestions, it is respectfully requested that the Examiner contact the undersigned in order to expeditiously resolve any outstanding issues.

Attached hereto is a marked-up version of the changes made to the specification and claims by the current amendment. The attached page is captioned "**Version with Markings to Show Changes Made.**"

To the extent necessary, Applicants petition for an Extension of Time under 37 CFR 1.136. Please charge any fees in connection with the filing of this paper, including extension of time fees, to the deposit account of Texas Instruments Incorporated, Account No. 20-0668.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'Peter K. McLarty', with a long horizontal flourish extending to the right.

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**Version with Markings to Show Changes Made**

**IN THE SPECIFICATION**

Please replace the paragraph beginning at page 6, line 11, with the following rewritten paragraph:

--The results found with this structure are surprisingly different from those found with high-energy retrograde wells: the results reported with high-energy retrograde wells did not show any major improvement over that for more conventional Ldmos. [(See the Zhu and Hower et al. papers in the proceedings of ISPSD 2000, both of which are hereby incorporated by reference.)]—

Please replace the paragraph beginning at page 1, line 1, with the following rewritten paragraph:

--This application claims priority from provisional 60/259,322 filed 12/31/00, which is hereby incorporated by reference. [Priority is also claimed from copending PCT application \_\_\_\_\_ (TI-30010PC), which also claims priority from provisional 60/259,322, and in which the US is a designated country.]--

Please replace the paragraph beginning at page 16, line 13 with the following rewritten paragraph:

-- Figures 5A through [5E] 5C are a set of device cross-sections, showing how the device dimensions are scaled for different operating voltage specifications. However, note that the drift region length will scale with voltage (approximately one micron for each 25V), and this increase in length has not been shown. --

Please replace the paragraph beginning on page 16, line 8 with the following rewritten paragraph:

-- Metallization 419 (e.g. 500 to 800 nm of Al/Si/TiW stack) is then deposited, patterned and etched. As shown in Figure 4H, the metallization structure 419 connects the source 18 with the buried body 30. This produces the device structure of Figure 4H. Processing is then completed with conventional steps for further metallization if desired, encapsulation, contact pad exposure, etc. --